MOSFET

Metal Oxide Semiconductor Field Effect Transistor

Bare Die

OptiMOS™3 Power MOS Transistor Chip
IPC218N04N3

Data Sheet

Rev. 2.5
Final

Industrial & Multimarket

1 Description

- N-channel enhancement mode
- For dynamic characterization refer to the datasheet of IPB011N04N G
- AQL 0.65 for visual inspection according to failure catalogue
- Electrostatic Discharge Sensitive Device according to MIL-STD 883C
- Die bond: soldered or glued
- Backside metallization: NiV system
- Frontside metallization: AlCu system
- Passivation: Nitride + Imide

Power MOS Transistor Chip

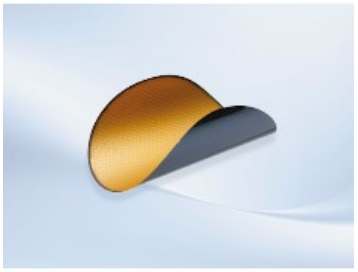
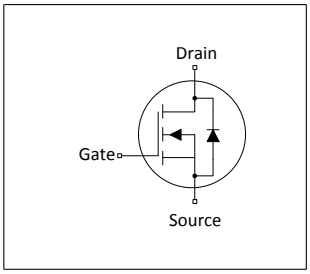


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{(BR)DSS}$	40	V
$R_{DS(on)}$	1.1[1)]	mΩ
Die size	5.9 x 3.7	mm^2
Thickness	175	µm



Type / Ordering Code	Package	Marking	Related Links
IPC218N04N3	Chip	not defined	-

2 Electrical Characteristics on Wafer Level

at T_j = 25°C, unless otherwise specified

Table 2

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	40	-	-	V	V_{GS}=0 V ,I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	2	-	4	V	V_{DS}=V_{GS}, I_D=200 µA
Zero gate voltage drain current	I_{DSS}	-	0.1	2	µA	V_{GS}=0 V ,V_{DS}=40 V
Gate-source leakage current	I_{GSS}	-	2	200	nA	V_{GS}=20 V ,V_{DS}=0 V
Drain-source on- resistance	$R_{DS(on)}$	-	0.5[2)]	50[3)]	mΩ	V_{GS}=10 V ,I_D=2.0 A
Reverse diode forward on-voltage	V_{SD}	-	0.86	1.1	V	V_{GS}=0 V ,I_F=1A
Internal gate resistance	R_G	-	1.5	-	Ω	-
Avalanche energy, single pulse	E_{AS}	-	-	525[4)]	mJ	I_D =50 A, R_{GS} =25 Ω

[1)] packaged in a PG-TO263-7 (see ref. product)
[2)] typical bare die $R_{DS(on)}$; V_{GS}=10 V when used with 4*500µm Al-wedge double-stitch bonding
[3)] limited by wafer test-equipment
[4)] Wafer tested. For general avalanche capability refer to the datasheet of IPB011N04N G

3 Package Outlines

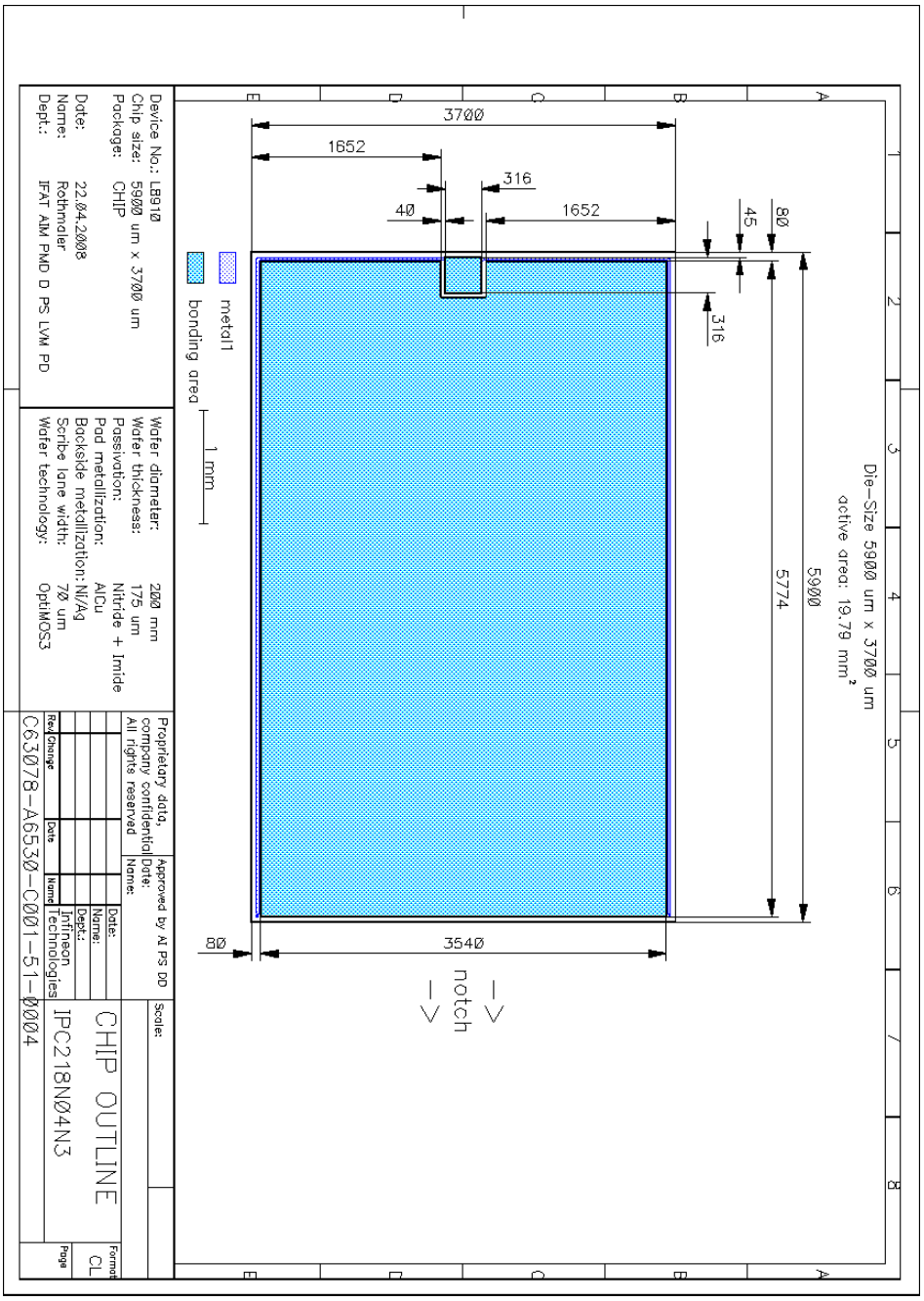


Figure 1 Outline Chip, dimensions in µm

Revision History

IPC218N04N3

Revision: 2014-07-25, Rev. 2.5

Previous Revision		
Revision	Date	Subjects (major changes since last revision)
2.5	2014-07-25	Release Final Version

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